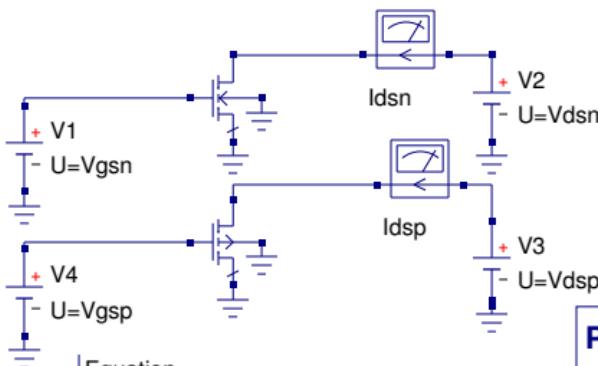EKV26nMOS1
LEVEL=2
L=10e-6
W=10e-6
Vto=0.6
Gamma=0.71
Phi=0.97
Kp=50e-6
Theta=50e-3

EKV26pMOS1
LEVEL=2
L=10e-6
W=25e-6
Vto=-0.55
Gamma=0.69
Phi=0.87
Kp=20e-6
Theta=50e-3

dc simulation

DC1

V1
U=Vgsn

V4
U=Vgsp

Idsn

Idsp

V2
U=Vdsn

V3
U=Vdsp

Equation

Eqn1
Ids_pMOS_3D=PlotVs(Idsp.I, Vgsp, Vdsp)
Ids_pMOS=PlotVs(Idsp.I, Vgsp, Vdsp)
Ids_nMOS=PlotVs(Idsn.I, Vgsn, Vdsn)
Vdsp=-Vdsn
Vgsp=-Vgsn
Ids_nMOS_3D=PlotVs(Idsn.I, Vgsn, Vdsn)

Parameter sweep

SW2
Sim=DC1
Type=lin
Param=Vdsn
Start=0
Stop=3
Points=61

Parameter sweep

SW1
Sim=SW2
Type=lin
Param=Vgsn
Start=0
Stop=3
Points=17